

# **AP3403A 30V P-Channel Enhancement Mode MOSFET**

SOT23

## **General Description**

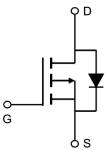
AP3403A combines advanced MOSFET technology with a low resistance package to provide extremely low  $R_{\text{DS(ON)}}$ . This device is most suitable to load-switch or PWM applications.

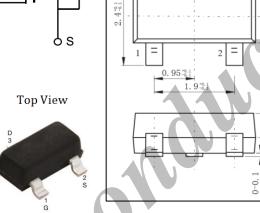
## **Applications**

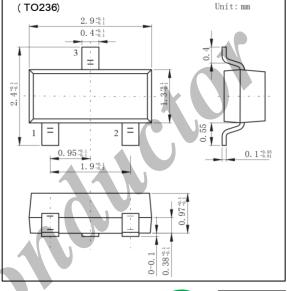
- DC/DC converter for portable devices
- Load switch

#### **Product Summary**

$V_{DS}$	-30V
In (at $V_{GS} = -10V$ )	-2.6A
$R_{DS(ON)}$ (at $V_{GS} = -10V$ )	$< 115 \mathrm{m}\Omega$
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$ )	$< 150 \mathrm{m}\Omega$
$R_{DS(ON)}$ (at $V_{GS} = -2.5V$ )	$<200 m\Omega$











# Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DS}$	-30	V	
Gate-Source Voltage	$V_{GS}$	±12	V	
Continuous Drain Current T <sub>A</sub> =25°C		-2.6		
T <sub>A</sub> =70°C	I <sub>D</sub>	-2.2	Α	
Pulsed Drain Current *	I <sub>DM</sub>	-13		
Power Dissipation T <sub>A</sub> = 25°C	D	1.4	W	
T <sub>A</sub> = 70°C	$P_{D}$	0.9		
Thermal Resistance. Junction-to-Ambient t≤10s	В	90		
Thermal Resistance. Junction-to-Ambient (Stead-state)	$R_{ hetaJA}$	125	°C/W	
Thermal Resistance. Junction-to-Lead (Stead-state)	$R_{ heta_{JL}}$	80		
Junction Temperature	Τι	150	°C	
Storage Temperature Range	Тѕтс	-55 to 150		

<sup>\*</sup> Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>I</sub>=25°C.



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#### • Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D$ =-250 $\mu$ A, $V_{GS}$ =0V	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-30V, $V_{GS}$ =0V			-1	
		$V_{DS}$ =-30V, $V_{GS}$ =0V, $T_{J}$ =55°C		_	-5	μA
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0V$ , $V_{GS}=\pm 12V$			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-0.6	-1	-1.4	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =-10V, $I_{D}$ =-2.6A		88	115	mΩ
		$V_{GS}$ =-10V, $I_{D}$ =-2.6A $T_{J}$ =125°C		143	200	
		$V_{GS}$ =-4.5V, $I_D$ =-2A		103	150	
		$V_{GS}$ =-2.5V, $I_{D}$ =-1A		139	200	
On state drain current	$I_{D(ON)}$	$V_{GS}$ =-10V, $V_{DS}$ =-5V	-13			A
Forward Transconductance	$\mathbf{g}_{ ext{FS}}$	$V_{DS}$ =-5V, $I_{D}$ =-2.6A		8		S
Input Capacitance	$C_{\mathrm{iss}}$	$\begin{array}{c c} \hline C_{iss} \\ \hline C_{oss} \\ \hline C_{rss} \\ \end{array} V_{GS} = 0 \text{V, V}_{DS} = -15 \text{V, f} = 1 \text{MHz}$		260	315	pF
Output Capacitance	$C_{oss}$			37		
Reverse Transfer Capacitance	$C_{rss}$			20		
Gate Resistance	$R_{g}$	$V_{GS}$ =0V, $V_{DS}$ =0V, $f$ =1MHz	4	8	12	Ω
Total Gate Charge (10V)	0			5.9	7.2	
Total Gate Charge (4.5V)	$Q_{\mathrm{g}}$	$-V_{GS}$ =-10V, $V_{DS}$ =-15V, $I_{D}$ =-2.6A		2.8	3.5	nC
Gate Source Charge	$Q_{gs}$			0.7		
Gate Drain Charge	$Q_{\mathrm{gd}}$			1		
Turn-On Delay Time	t <sub>D(on)</sub>			6		
Turn-On Rise Time	$t_{\rm r}$	$V_{GS}$ =-10V, $V_{DS}$ =-15V,		3.5		ns
Turn-Off Delay Time	$t_{\mathrm{D(off)}}$	$t_{D(off)}$ $R_L$ =5.76 $\Omega$ , $R_{GEN}$ =3 $\Omega$		20		
Turn-Off Fall Time	$t_{f}$			5		
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F$ =-2.6A, $d_I/d_t$ =100A/ $\mu$ s		11.5	15	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F$ =-2.6A, $d_I/d_t$ =100A/ $\mu$ s		4.5		nC
Maximum Body-Diode Continuous Current	$I_S$				-1.5	A
Diode Forward Voltage	$V_{SD}$	$I_S$ =-1A, $V_{GS}$ =0V		-0.78	-1	V

## Ordering Information

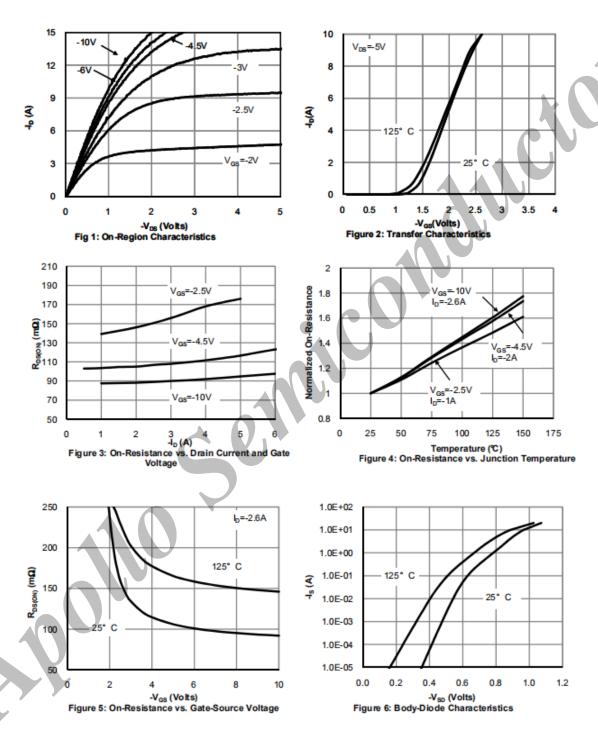
Ordering Part Number	Package	MOQ
AP3403A	SOT23 (TO236)	3,000 pcs / reel

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## **30V P-Channel Enhancement Mode MOSFET**

## • Typical Characteristics



The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.



#### • Typical Characteristics

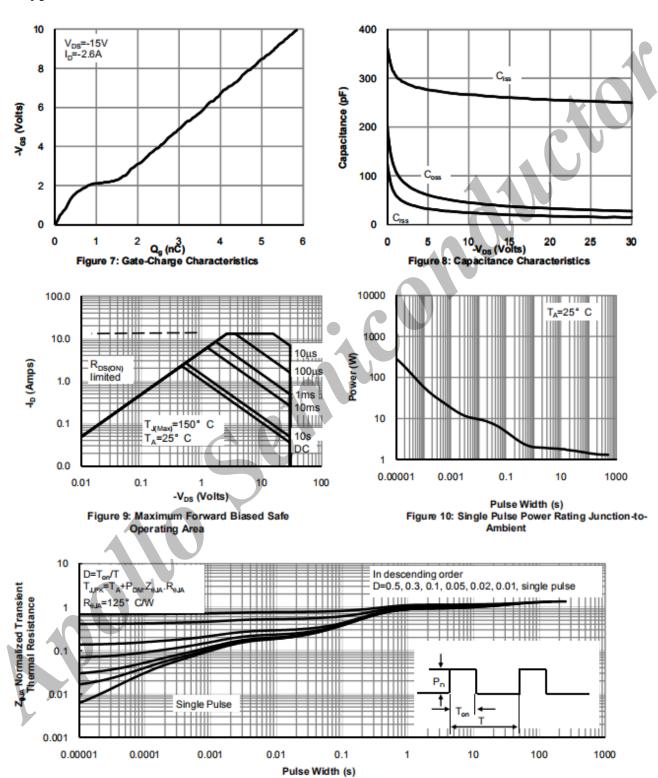


Figure 11: Normalized Maximum Transient Thermal Impedance



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